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Hysteresis in the transfer characteristics of MoS₂ transistors

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#	Paper	IF	Citations
177	Novel circuit design for high-impedance and non-local electrical measurements of two-dimensional materials. 2018 , 89, 024705		1
176	Quantitative analysis of trap states through the behavior of the sulfur ions in MoS ₂ FETs following high vacuum annealing. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 105102	3	4
175	Highly sensitive MoS photodetectors with graphene contacts. <i>Nanotechnology</i> , 2018 , 29, 20LT01	3.4	25
174	P-Type Doping of WS ₂ Quantum Dots via Pulsed Laser Ablation. 2018 , 5, 4828-4837		9
173	Environmental Effects on the Electrical Characteristics of Back-Gated WSe ₂ Field-Effect Transistors. <i>Nanomaterials</i> , 2018 , 8,	5.4	38
172	Van der Waals junction field effect transistors with both n- and p-channel transition metal dichalcogenides. <i>Npj 2D Materials and Applications</i> , 2018 , 2,	8.8	39
171	Traps induced memory effect in rubrene single crystal phototransistor. <i>Applied Physics Letters</i> , 2018 , 113, 103301	3.4	16
170	Gas adsorbates are Coulomb scatterers, rather than neutral ones, in a monolayer MoS field effect transistor. <i>Nanoscale</i> , 2018 , 10, 10856-10862	7.7	6
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